# 2SA2102

# Silicon PNP epitaxial planar type

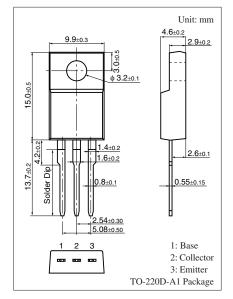
Power supply for Audio & Visual equipments such as TVs and VCRs Industrial equipments such as DC-DC converters

#### Features

- High-speed switching (t<sub>stg</sub>: storage time/t<sub>f</sub>: fall time is short)
- $\bullet$  Low collector-emitter saturation voltage  $V_{CE(\text{sat})}$
- $\bullet$  Superior forward current transfer ratio  $h_{F\!E}$  linearity
- TO-220D built-in: Excellent package with withstand voltage 5 kV guaranteed

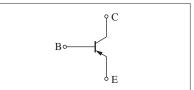
<b>.</b>								
Parameter	Symbol	Rating	Unit					
Collector-base voltage (Emitter open)		V <sub>CBO</sub>	-60	V				
Collector-emitter voltage (Base open)		V <sub>CEO</sub>	-60	V				
Emitter-base voltage (Collector open)		V <sub>EBO</sub>	-6	V				
Collector current		I <sub>C</sub>	-3	А				
Peak collector current		I <sub>CP</sub>	-5	А				
Collector power	$T_C = 25^{\circ}C$	P <sub>C</sub>	15	W				
dissipation	$T_a = 25^{\circ}C$		2					
Junction temperature		Tj	150	°C				
Storage temperature		T <sub>stg</sub>	-55 to +150	°C				

#### Absolute Maximum Ratings $T_C = 25^{\circ}C$



#### Marking Symbol: A2102

#### Internal Connection



## Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = 0$	-60			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = -60 \text{ V}, I_E = 0$			-100	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = -60 \text{ V}, I_B = 0$			-100	μΑ
Forward current transfer ratio	h <sub>FE1</sub>	$V_{CE} = -4 V, I_C = -0.2 A$	60			—
	h <sub>FE2</sub>	$V_{CE} = -4 V, I_C = -1 A$	80		250	—
	h <sub>FE3</sub>	$V_{CE} = -4 V, I_C = -3 A$	30			—
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{C} = -3 A, I_{B} = -0.375 A$			- 0.8	V
Transition frequency	f <sub>T</sub>	$V_{CE} = 10 \text{ V}, I_C = -0.1 \text{ A}, f = 10 \text{ MHz}$		100		MHz
Turn-on time	ton	$I_C = -1$ A, Resistance loaded		0.2		μs
Storage time	t <sub>stg</sub>	$I_{B1} = -0.1 \text{ A}, I_{B2} = 0.1 \text{ A}$		0.4		μs
Fall time	t <sub>f</sub>	$V_{\rm CC} = -50 \text{ V}$		0.1		μs

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

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